

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	236	(257/736).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/03 13:31
L4	5	("20020019117" "6,475,456" "6,416,578").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 17:03
L5	3	("5248385"   "5723378").PN. OR ("6475456").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/08/03 13:31
L6	17	("5248385").URPN.	USPAT	OR	ON	2006/08/03 13:31
L7	9	("4912064"   "4946547"   "5122223"   "5230768"   "5248385"   "5501173"   "5747831"   "5915194"   "6416578").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/08/03 13:31
L8	2	"6475456".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L9	2	"20040164380"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L10	3286976	planar near\$2 defect near\$2 density same (silico semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L11	3314152	planar near\$2 defect near\$2 density same (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L12	3236723	planar near\$2 defect near\$2 density with single adj crystal same (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31

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L13	3235979	planar near\$2 defect near\$2 density with single adj crystal with region same (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L14	3236642	planar near\$2 defect near\$2 density with single adj crystal with (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L15	3235965	planar near\$2 defect near\$2 density with single adj crystal with region with (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L16	3235852	planar near\$2 defect near\$2 density with single adj crystal with low adj region with (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L17	3235852	planar near\$2 defect near\$2 density WITH single adj crystal WITH low adj region WITH (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L18	0	planar adj defect adj density WITH single adj crystal WITH low adj region WITH (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L19	2460250	planar With defect near\$2 density WITH single adj crystal WITH low adj region WITH (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L20	2376826	planar near\$1 defect adj density WITH single adj crystal WITH low adj region WITH (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L21	0	planar with defect with density WITH single adj crystal WITH low adj region WITH (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31

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L22	18	planar with defect with density WITH single adj crystal same (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L23	2459347	planar near defect near\$2 density WITH single adj crystal WITH low adj region WITH (silicon semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L24	347	(117/106).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/03 13:31
L25	2459442	planar near defect near\$2 density and L24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L26	4872	planar with defect wiht density and L24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L27	2	planar with defect with density and L24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L28	9	("20020014198"   "20020019117"   "20020072249"   "20020096104"   "5254370"   "5390626"   "6416578"   "6442184").PN. OR ("6736894"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/08/03 13:31
L29	2	"20030111670".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L30	33	planar with defect with density same (silico semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31

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L31	281	(257/617).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/03 13:31
L32	1	planar with defect with density and L31	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 17:08
L33	1366729	planar adj\$2 defect adj\$2 density same (silico semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L34	52	planar with defect with density and "257"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:31
L36	0	electron with conecration with defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 13:43
L37	253	electron with concentration with defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 14:00
L38	218	37 and (semiconductor or siliocn si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 14:01
L39	228	37 and (semiconductor or silicon si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 14:03

## EAST Search History

L40	35	(US-20040113271-\$ or US-20020014198-\$ or US-20020110997-\$ or US-20050189561-\$ or US-20050189562-\$ or US-20030173680-\$ or US-20040063240-\$ or US-20040212057-\$ or US-20010033022-\$ or US-20040178501-\$ or US-20020182773-\$ or US-20020171130-\$ or US-20010042906-\$).did. or (US-6596080-\$ or US-5835355-\$ or US-6165874-\$ or US-5915194-\$ or US-5363800-\$ or US-6475456-\$ or US-5317176-\$ or US-6933545-\$ or US-4833512-\$ or US-6512304-\$ or US-6774466-\$ or US-6825548-\$ or US-6416578-\$ or US-5393705-\$ or US-5073817-\$ or US-6093970-\$ or US-6891256-\$ or US-6278176-\$ or US-5248385-\$).did. or (EP-573297-\$).did. or (JP-08148526-\$).did. or (EP-704896-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/03 14:00
L41	0	40 and electron with concentration with defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 17:06
L42	0	40 and electron with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 14:00
L43	15	37 and (semiconductor or silicon si)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 14:03
L44	0	40 and electron near2 concentration with defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 14:03
L45	0	electron near2 concentration with defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 14:03

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L46	65	electron near2 concentration with defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 14:04
L47	2	"20040164380".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 17:03
L48	270	(438/736).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/03 17:06
L49	470	(438/471).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/03 17:06
L50	1	49 and electron with concentration with defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 17:08
L51	0	(defect and density and compound and single and crytal and electron and concentration).clm.	US-PGPUB; USPAT	OR	ON	2006/08/03 17:13
L52	1	(defect and density and compound and semiconductor and electron and concentration).clm.	US-PGPUB	OR	ON	2006/08/03 17:10
L53	2	(defect and compound and semiconductor and electron and concentration).clm.	US-PGPUB	OR	ON	2006/08/03 17:10
L54	0	(defect and density and compound and single and crytal and gradient and (transition boundary interphase)).clm.	US-PGPUB; USPAT	OR	ON	2006/08/03 17:12
L55	5	(defect and density and compound and gradient and (transition boundary interphase)).clm.	US-PGPUB; USPAT	OR	ON	2006/08/03 17:12
L56	2	(defect and density and compound and gradient and (transition boundary interphase)).clm.	US-PGPUB	OR	ON	2006/08/03 17:12
L57	1994	(defect and density and compound and single and crytal ohmic).clm.	US-PGPUB	OR	ON	2006/08/03 17:13

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<i>L58</i>	<i>0</i>	<i>(defect and density and compound and single and crytal and ohmic).clm.</i>	<i>US-PGPUB</i>	<i>OR</i>	<i>ON</i>	<i>2006/08/03 17:13</i>
<i>L59</i>	<i>2</i>	<i>(defect and density and compound and semiconductor and ohmic).clm.</i>	<i>US-PGPUB</i>	<i>OR</i>	<i>ON</i>	<i>2006/08/03 17:14</i>
<i>L60</i>	<i>2</i>	<i>(defect and density and compound and ohmic).clm.</i>	<i>US-PGPUB</i>	<i>OR</i>	<i>ON</i>	<i>2006/08/03 17:14</i>